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Index

[More information](#)

501

Author Index

- Adrian, F.J., 343
 Aka, B., 361
 Arjavalingam, G., 81
 Arnold, G.W., 453, 469
 Ashby, C.I.H., 429, 469
 Auvert, G., 125, 131

 Baiocchi, F.A., 291
 Baseman, R.J., 237
 B uerle, D., 411
 Baufay, L., 89
 Bedair, S.M., 285
 Beggy, J.C., 291
 Bent, B.E., 177
 Bernoux, F., 403
 Biefeld, R.M., 313
 Blonder, G.E., 183
 Boch, E., 361
 Bohandy, J., 343
 Bouree, J.E., 49, 55
 Brannon, J.H., 27
 Brannon, P.J., 469
 Bresse, J.F., 49
 Brewer, P.D., 319, 327

 Cacouris, T., 43
 Campisi, G.J., 101
 Caolo, M.A., 21
 Carnera, A., 453
 Chabal, Y.J., 201
 Chen, L., 463
 Chenglu, L., 487
 Chera, J.J., 159
 Chow, T.P., 495
 Collins, G.J., 21
 Comita, P.B., 249

 Daghighi-Ruhi, R., 221
 Datta, M., 449
 Ding, L., 487
 Donnelly, V.M., 291
 Doss, K., 435
 Dubner, A.D., 255
 Dubois, L.H., 177
 Dulcey, C.S., 301

 Eden, J.G., 349
 Ehrlich, D.J., 13
 El-Masry, N., 285
 Engelsberg, A.C., 159
 Eres, D., 355
 Eyett, M., 411

 Farrow, R.C., 291
 Ferrieu, F., 403

 Fleming, C.G., 183
 Flicstein, J., 49, 55
 Fogarassy, E., 361
 Freedman, A., 331
 Fridmann, S., 33
 Friend, C.M., 201
 Fuchs, C., 361

 Gamo, K., 261, 477
 Ge, L., 113
 Geohegan, D.B., 355
 George, T.F., 267
 Green, W.J., 343
 Greene, J.E., 153
 Gross, M.E., 89
 Gupta, A., 95, 237

 Habekost, A., 221
 Halliwell, M., 101
 Harriott, L.R., 483
 Harris, T.D., 291
 Harumoto, H., 195
 Heidberg, J., 221
 Herman, I.P., 113, 119
 Higashi, G.S., 183
 Higashikawa, I., 3
 Hiraoka, H., 21
 Hirata, K., 397
 Hirata, M., 61
 Horiike, Y., 3
 Horioka, K., 3
 Hurst, Jr., J.E., 81

 Ishikawa, J., 391
 Ito, S., 3

 Jackson, R.L., 207
 Jagannathan, R., 95
 Jaing, B., 285
 Jelski, D.A., 267
 Jensen, J.E., 319, 327
 Jensen, K.F., 107
 Jervis, T.R., 243
 Joyce, Jr., E.L., 243

 Karam, N.H., 285
 Katsuyama, T., 285
 Kawai, S., 397
 Kawasaki, M., 217, 231, 459
 Kawate, Y., 367
 Kiely, C.J., 349
 Killeen, K.P., 313
 Kim, B.F., 343
 Kishida, S., 61
 Kodas, T.T., 249

Cambridge University Press

978-1-107-41104-3 - Laser and Particle-Beam Chemical Processing for Microelectronics:

Symposium held December 1-3, 1987, Boston, Massachusetts, U.S.A.

Edited by Daniel J. Ehrlich, Gregg S. Higashi and Modest M. Oprysko

Index

[More information](#)

502

- Kolzer, U., 411
 Konagai, M., 307
 Korenowski, G.M., 159
 Kotecki, D.E., 119
 Krchnavek, R.R., 43
 Krishnaswamy, J., 21
 Kullmer, R., 411
 Küper, S., 139
 Kurabayashi, T., 275
 Kwok, H.S., 337

 Lam, C., 189
 Lamont, M.G., 291
 Li, L., 21
 Liberman, V., 463
 Lin, C-M., 495
 Lin, M.C., 301
 Liu, H., 285
 Lowndes, D.H., 355
 Lu, T.-M., 189
 Lubben, D., 153
 Lyons, A.M., 67

 Mantell, D.A., 165, 171
 Mashburn, D.N., 355
 Matsumoto, K., 61
 Matsushima, T., 459
 Mattocks, P., 337
 Mazzi, G., 453
 Mazzoldi, P., 453
 McCrary, V.R.,
 Melngailis, J., 255
 Mendenhall, F.T., 67
 Miller, B.J., 379, 385
 Mingxin, Q., 487
 Miracky, R.F., 435
 Mogyrosi, P., 411
 Moorjani, K., 343
 Mori, K., 217
 Morishige, Y., 61
 Motooka, T., 153
 Myers, D.R., 429

 Nakamatsu, H., 397
 Nakase, M., 3
 Nakaue, A., 367
 Namba, S., 261, 477
 Natzle, W.C., 213
 Nguyen, S.V., 33
 Nishizawa, J., 275
 Nonaka, M., 3
 Nuzzo, R.G., 177

 O'Neill, J.A., 463
 Oka, T., 231
 Olson, G.L., 319, 327
 Oprysko, M.M., 81
 Orlowski, T.E., 165, 171
 Osgood, Jr., R.M., 43, 421, 463

 Padmanabhan, R., 379, 385
 Partridge, J.P., 443
 Pauleau, Y., 125
 Pazonis, G.D., 113
 Pehrsson, P.E., 101
 Petzold, H.-C., 75
 Piglmayer, K., 411
 Podlesnik, D.V., 421
 Pougnet, A.M., 49
 Progler, C., 237
 Putzar, R., 75

 Rembetski, J., 33
 Ro, J.S., 255
 Romankiw, L.T., 449
 Rotel, M., 101
 Rothschild, M., 13
 Rozgonyi, G.A., 285

 Saha, N.C., 385
 Salaneck, W.R., 153
 Salih, A.S.M., 285
 Sameshima, T., 491
 Sato, H., 217, 231, 459
 Sato, T., 3
 Sausa, R.C., 237
 Scarmozzino, R., 43
 Scelsi, G., 43
 Schmidt, M.T., 421
 Shaw, D.T., 337
 Shi, L., 337
 Shinzawa, T., 61
 Siffert, P., 361
 Skouby, D.C., 107
 Squire, D.W., 301
 Steckl, A.J., 495
 Stehle, J.L., 403
 Stinespring, C.D., 331
 Strutt, P.R., 443
 Stuke, M., 139
 Sundgren, J.-E., 153
 Suzuki, H., 217
 Swanson, J.R., 201

 Tachibana, H., 367
 Takagi, T., 195, 391
 Takahashi, K., 307
 Takai, M., 261
 Takaoka, G.H., 391
 Tam, G., 379
 Tamir, S., 101
 Tang, H., 113
 Tavitian, V., 349
 Thomas, O., 403
 Thompson, C.V., 255
 Tokuda, J., 261
 Tokumitsu, E., 307
 Tonneau, D., 125, 131
 Toya, K., 231

Cambridge University Press

978-1-107-41104-3 - Laser and Particle-Beam Chemical Processing for Microelectronics:

Symposium held December 1-3, 1987, Boston, Massachusetts, U.S.A.

Edited by Daniel J. Ehrlich, Gregg S. Higashi and Modest M. Oprysko

Index

[More information](#)

503

Tu, C.W., 291
Tutt, L.W., 319, 327
Tyndall, G.W., 207

Uesugi, F., 61
Usui, H., 195
Usui, S., 491

Vasile, M.J., 483
Vigliotti, D.R., 449
von Gutfeld, R.J., 449
von Weyssenhoff, H., 221

Wang, X.W., 337
Weigmann, U., 75
Wendelken, J.F., 153
Wilke, I., 75
Wilkins, Jr., C.W., 67
Witanachchi, S., 337
Wong, J., 189
Wu, C.-H., 373
Wu, Z.C., 267

Xu, Z., 477
Xuebiao, L., 487

Yamada, H., 61
Yamada, I., 195
Yamada, T., 307
Yang, E.S., 421
Ying, Q.Y., 337
Yoshida, I., 285
Yu, C.F., 421

Zahavi, J., 101
Zhang, Y., 139
Zheng, J.P., 337
Zhengzhuo, Z., 487
Zinck, J.J., 319, 327
Zuhoski, S.P., 313

Cambridge University Press

978-1-107-41104-3 - Laser and Particle-Beam Chemical Processing for Microelectronics:
Symposium held December 1-3, 1987, Boston, Massachusetts, U.S.A.

Edited by Daniel J. Ehrlich, Gregg S. Higashi and Modest M. Oprysko

Index

[More information](#)

Cambridge University Press

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Symposium held December 1-3, 1987, Boston, Massachusetts, U.S.A.

Edited by Daniel J. Ehrlich, Gregg S. Higashi and Modest M. Oprysko

Index

[More information](#)

505

Subject Index

- a-carbon deposition, 367
- a-Si deposition, 355
- ablation
 - BaTiO₃, 411
 - femtosecond, 139
 - LiNbO₃, 411
 - polymer, 139
- absorption cross-sections, 307, 367
- adatom mobility, 349
- adsorbed phase
 - Br₂, 459
 - Cl₂, 463
 - I₂, 459
 - trimethylaluminum, 153, 159, 165
 - trimethylgallium, 217
- Al
 - alkyl photochemistry, 139
 - deposition, 165, 171, 177, 183, 189, 195, 307
 - direct writing, 43, 49, 55
 - etching, 483
 - interconnects, 43
 - islands, 171
- Al(C₂H₅)₃, 139
- Al(C₄H₉)₃, 139, 171, 177, 183, 307
- Al(CH₃)₂H, 43
- Al(CH₃)₃, 49, 55, 139, 151, 159, 165
- Al/Si interface, 183, 195
- Al₂O₃, 391, 397
 - deposition, 391
- AlAs deposition, 307
- AlGaAs deposition, 291
- alkylsilanes, 177
- alkyltellurides, 327
- AlN deposition, 391
- aluminothermic reaction, 487
- AsCl₃, 275
- AsH₃, 275, 285, 301
- atomic layer epitaxy, 285
- Au
 - deposition, 195, 237
 - direct writing, 81, 101, 249, 255
- B laser doping, 491
- BaTiO₃
 - ablation, 411
 - surface reduction, 411
- benzene, 231
- benzoic acid, 453
- beta-hydride elimination, 177, 307
- Br₂, 459
- broad area electron source, 21
- butyl radical production, 307
- C₂H₃Cl, 367
- carbon, 67
- carbon interconnections, 67
- carrier recombination, 429
- CCl₄, 367
- Cd(CH₃)₂, 319, 331
- CdS_xSe(1-x) deposition, 337
- CdTe deposition, 319, 327, 331
- chemical processes, 373
- chemical vapor deposition, 61, 81, 119, 177, 183, 243, 249, 261, 301, 355, 361, 367, 373, 379, 385, 397
- chemisorption, 159, 331
- Cl₂, 33, 411, 463
- composition control, 337
- computer simulation, 107, 131
- contact formation, low resistivity, 61
- Cr
 - deposition, 237
 - etching, 483
- Cr(CO)₆, 207, 213
- critical fields, 267
- cross-section, two-photon, 361
- Cu, 27
 - deposition, 237
 - direct writing, 95
 - etching, 435, 463
 - formate, 95
 - oxidation, 95
- damage-controlled etching, 429, 469
- deposition (see also direct writing)
 - a-carbon, 367
 - a-Si, 355
 - Al, 165, 171, 177, 183, 189, 195, 307
 - Al₂O₃, 391
 - AlAs, 307
 - AlGaAs, 291
 - AlN, 391

Cambridge University Press

978-1-107-41104-3 - Laser and Particle-Beam Chemical Processing for Microelectronics:
Symposium held December 1-3, 1987, Boston, Massachusetts, U.S.A.

Edited by Daniel J. Ehrlich, Gregg S. Higashi and Modest M. Oprysko

Index

[More information](#)

506

- Au, 195
- Au, Cu, Cr, Ti, Ta, Pt, Ni, 237
- by laser ablation, 343
- $\text{CdS}_x\text{Se}_{(1-x)}$, 337
- CdTe , 319, 327, 331
- epitaxial Ge, 349
- Fe, 201
- from electroplating solutions, 101
- GaAs, 275, 285, 291, 301
- InSb, 313
- modeling, 107
- $\text{Ni/Ni}_3\text{C}$, 243
- perovskite superconductors, 343
- Pt, Ir, 221
- SiC, 397
- SiN, 379, 391
- SiO_2 , 385
- tin oxide, 261
- using solid sources, 337
- W, 201
- desorption spectroscopy, 463
- dielectric breakdown, 243, 443
- dimethyl-aluminum hydride, 43
- dimethyl-gold-hexafluoroacetylacetonate, 81, 249
- diode laser direct writing, 81
- direct ion doping, 495
- direct writing (see also deposition)
 - Al, 43, 49, 55
 - Au, 81, 101, 249, 255
 - carbon, 67
 - Cu, 95
 - Mo, 61
 - modeling, 107, 131
 - Pd, 89
 - Si, 119, 125
 - SiO_2 , 125
 - SiN, 125
 - Sn, 75
 - ultraviolet laser, 43, 49, 55
 - using diode lasers, 81
 - W, 75
- dopant diffusion, 491
- dry etching, 459
- elastic recoil detection, 453
- electromigration resistance, 195
- electron beam processing, 21
- electron/molecule interactions, 231
- epitaxial Al films, 195
- etching (see also ablation)
 - Al, 483
 - Cr, 483
 - Cu, 27, 435, 463
 - GaAs, 429
 - LiNbO_3 , 469
 - liquid phase, 435, 449
 - mechanisms, 33
 - poly-Si, 33
 - projection, 27, 33
 - quantum yield, 429
 - Si, 27, 411, 477
 - SiO_2 , 477
 - steel/stainless steel, 449
- excimer laser
 - deposition - see deposition
 - etching, 27, 33
 - lithography, 3, 13
- Fe deposition, 201
- $\text{Fe}(\text{CO})_5$, 201
- femtosecond laser, 139
- focussed ion-beams, 255, 483, 495
- Ga atom production, 217, 301
- Ga doped P⁺n diode, 495
- $\text{Ga}(\text{C}_2\text{H}_5)_3$, 275, 291
- $\text{Ga}(\text{CH}_3)_3$, 217, 275, 285, 301
- GaAs
 - deposition, 275, 285, 291, 301
 - etching, 261, 429
 - MESFETs, 379
 - oxides, 421
 - passivation, 379, 421
- $\text{GaAs}(100)$, 291, 319, 331, 349
- Ge deposition, 349
- GeH_4 photolysis, 349
- Ginzburg-Landau theory, 267
- grating amplitudes, 267
- growth mechanisms, 107, 119, 301, 355, 361, 373
- heat transfer, 243
- hexamethylcyclotrisilazane, 443
- Hg-photosensitization, 373, 379, 385
- hydrogen, effect of, 49, 55, 165, 477
- I_2 , 459
- implant damage profiling, 469
- $\text{In}(\text{CH}_3)_3$, 313
- in-situ diagnostics, 113, 153, 403
- infrared absorption, 159, 221, 275
- InSb deposition, 313
- interconnections
 - Al, 43

Cambridge University Press

978-1-107-41104-3 - Laser and Particle-Beam Chemical Processing for Microelectronics: Symposium held December 1-3, 1987, Boston, Massachusetts, U.S.A.

Edited by Daniel J. Ehrlich, Gregg S. Higashi and Modest M. Oprysko

Index

[More information](#)

507

- carbon, 67
- LSI, 61
- interdiffusion, 487, 491
- ion
 - assisted etching, 477
 - beam induced deposition, 255
 - desorption, 463
 - images, 483
 - implantation, 495
 - scattering, 453
 - induced damage, 429, 469
 - molecule interactions, 231
 - surface interactions, 189, 195, 221, 429, 453, 469, 477
- ionized beam deposition, 189, 195, 221
- ionized cluster beam
 - deposition, 195, 221, 391
- Ir
 - acetylacetonate, 221
 - deposition, 221
- junction depth control, 491, 495
- kinetics, 107, 207, 249
- laser
 - ablation, 231, 343, 411
 - chemical etching, 449
 - controlled Al reduction, 487
 - deposition - see deposition
 - direct writing - see direct writing
 - doping, 491
 - enhanced surface migration, 275
 - evaporation deposition, 337, 343
 - heating, 113, 131
 - induced fluorescence, 217, 319, 327
 - induced forward transfer, 237
 - melting, Si, 491
 - oxidation, 421
- LiNbO₃
 - ablation, 411
 - etching, 469
 - proton exchange, 453
 - surface reduction, 411
- liquid phase etching, 435, 449
- lithography
 - excimer laser, 3, 13
 - x-ray, 75
- localized heating, 107, 131
- transient, 61, 243
- LSI interconnection, 61
- mask repair, 75, 255, 483
- mask technology, 483
- mass spectroscopy, 139, 165, 177, 221, 231, 249, 301, 307, 319, 373, 463, 483
- mechanism of film curing, 89, 95
- metal-organic
 - chemistry, 43, 177, 231, 301
 - chemical vapor deposition, 301, 307, 313, 319, 327, 331
- methyl radical production, 307
- microbalance, 207
- micromachining, 449
- microstructure of Au films, 255
- microwave analysis technique, 343
- Mn₂(CO)₁₀, 231
- Mo, 487
 - direct writing, 61
 - silicide, 487
- Mo(CO)₆, 61, 207
- modeling deposition, 107
- molecular beam epitaxy, 291, 307
- molecular layer epitaxy, 275, 285
- MoO₃, 487
- morphology, 213
- multi-level metallization, 183
- multiphoton ionization, 139, 221, 301
- N₂O, 385
- nanocrystals, 243
- nanophase particles, 243
- NH₃, 373
- Ni, 443
 - deposition, 237
- Ni(CO)₄, 243
- Ni/Ni₃C deposition, 243
- nonlinear integrated
 - optics, 337
- nucleation, 183
 - gas phase, 243
- optical modulators, 453
- optical multichannel
 - analysis, 403
- optics, 13
- oxide surfaces, 159
- passivation, 379

Cambridge University Press

978-1-107-41104-3 - Laser and Particle-Beam Chemical Processing for Microelectronics:
Symposium held December 1-3, 1987, Boston, Massachusetts, U.S.A.

Edited by Daniel J. Ehrlich, Gregg S. Higashi and Modest M. Oprysko

Index

[More information](#)

508

- patterned etching, 27
- patterning, submicron, 3, 13, 483
- Pd
 - acetate, 89
 - direct writing, 89
- periodic structure formation, 89
- perovskite superconductor deposition, 343
- photo-
 - assisted epitaxy, 275, 285, 291, 307, 319, 327
 - CVD, 373, 379, 385
 - chemical dry etching, 429
 - decomposition, 165, 171, 201, 207, 213, 221, 307, 313, 319, 327
 - deposition, 165, 171, 207, 213, 307, 331
 - desorption, 331
 - dissociation, single photon, 327
 - luminescence, 291, 397
- photolysis, 49, 55, 75, 119, 139, 153, 165, 171, 201, 207, 213, 217, 221, 307, 313, 319, 327, 331, 349, 355, 361, 367, 397
- photoresist, 3
- plasma
 - etching, 275
 - formation, 243, 443
- poly-Si etching, 33
- polyimide, 21, 27, 435
- polymer
 - ablation, 139
 - substrates, 67
- prenucleation, 171
- printed wiring boards, 67
- projection
 - etching, 27, 33
 - lens, achromatic, 3
 - patterned deposition, 237
- proton-exchanged LiNbO₃, 453
- Pt
 - acetylacetonate, 221
 - deposition, 221, 237
- pyrolysis, 61, 75, 81, 89, 119, 125, 131, 213, 249, 291, 301, 307, 313, 319, 331, 355, 443
- raman
 - microprobe, 113
 - spectroscopy of adsorbates, 159, 459
- rapid thermal annealing, 495
- reactant transport, 249
- reaction intermediates, 373, 397
- resist hardening, electron beam, 21
- room temperature deposition, 55
- salt solutions, 449
- Sb(CH₃)₃, 313
- Schottky
 - barrier heights, 421
 - contacts, 421
 - diode characteristics, 189
- secondary-ion mass spectroscopy, 483
- selective area deposition, 183
- short pulse laser, 61
- Si, 27, 113, 125, 355, 361, 487
 - direct writing, 119
 - etching, 411, 477
 - laser melting, 491
 - microstructures, 113
- Si(100), 153, 177, 331
- Si(111) (7X7), 201
- Si(111), 177
- Si₂H₆, 355, 361
- SiC epitaxy, 397
- SiH₄, 119, 361, 373, 385
- silicide, 237
 - formation, 443, 487
- silylamine, 373
- SiN, 125, 373, 379, 391
 - deposition, 379, 391
- SiO₂, 113, 125, 385
 - desorption, 385
 - etching, 477
- Sn direct writing, 75
- Sn(CH₃)₄, 75, 231
- SnCl₄, 261
- spectroscopic ellipsometry, 403
- sputter etching, 477
- stainless steel etching, 449
- Stokes/anti-Stokes scattering, 113
- strain, 113
- structured surfaces, 267
- submicron patterning, 13, 483
- superconductors, 267, 343
- supersonic expansions, 221
- surface
 - analysis, 153, 159, 165, 177, 201, 331, 379, 385, 403, 421
 - catalytic growth, 183
 - chemical reactions, 3, 177, 301, 331, 421, 487
 - coatings, 443
 - electronic structure, 153
 - hydroxyl groups, 159

Cambridge University Press

978-1-107-41104-3 - Laser and Particle-Beam Chemical Processing for Microelectronics:

Symposium held December 1-3, 1987, Boston, Massachusetts, U.S.A.

Edited by Daniel J. Ehrlich, Gregg S. Higashi and Modest M. Oprysko

Index

[More information](#)

509

photolysis, 153, 165, 171,
 217, 221, 331, 397
 reactions, 153, 159, 201,
 213, 217, 221, 249, 331,
 397
 reduction, BaTiO₃,
 LiNbO₃, 411
 temperature modulation, 249
 vibrational spectroscopy,
 153, 159, 201, 221, 459
 synchronized irradiation, 275,
 285

Ta deposition, 237
 Te atom production, 327
 Te(C₂H₅)₂, 319, 327
 Te(CH₃)₂, 327, 331
 temperature distribution, 75
 thermochemical etching, 261
 thin film analysis, 403
 Ti, 443
 deposition, 237
 time-resolved reflectivity,
 319
 tin oxide deposition, 261
 transition metal carbonyls,
 201, 221
 transport limited growth, 107
 tri-level resist process, 3
 triisobutylaluminum, 139,
 171, 177, 183, 307
 two-photon absorption, 361

ultraviolet
 absorption, 221, 313, 327
 laser direct writing, 43,
 49, 55

vapor phase epitaxy, 275,
 319, 327
 via hole filling, 183
 volcano-like deposits, 107

W
 deposition, 201
 direct writing, 75
 W(CO)₆, 75, 201, 207
 waveguides, 453

x-ray lithography, 75
 XeF₂, 477

YBa₂Cu₃O₇, 343